L	Hits	Search Text	DB	Time stamp
Number -	0	Fullford-Jim-H.in.	USPAT	2003/10/03
_	1	Fullford.in.	USPAT	2004/01/23
_	38360	semiconductor and ((depth or thickness)	USPAT	2004/01/23
-	`23673	same temperature) (semiconductor and ((depth or thickness)	USPAT	2002/09/11
_	14691	same temperature)) and (etch or etching) semiconductor and ((depth or thickness)	USPAT	2002/09/11
	5285	with temperature) (semiconductor and ((depth or thickness)	USPAT	2002/09/11
_	2028	with temperature)) and plasma ((semiconductor and ((depth or thickness)	USPAT	2002/09/11
		<pre>with temperature)) and plasma) and ((measur\$4 or compar\$3 or determin\$3)</pre>		10.00
_	1519	with (depth or thickness)) (((semiconductor and ((depth or	USPAT	2002/09/11
	·	thickness) with temperature)) and plasma) and ((measur\$4 or compar\$3 or determin\$3)		10.03
		with (depth or thickness))) and ((temperature or depth or thickness).ab.		
_	1177	(temperature or depth or thickness).clm.) (((semiconductor and ((depth or	USPAT	2002/09/11 16:03
		thickness) with temperature)) and plasma) and ((measur\$4 or compar\$3 or determin\$3)		10.03
		with (depth or thickness))) and ((depth or thickness).ab. (depth or		
_	607	thickness).clm.) ((((semiconductor and ((depth or	USPAT	2002/09/11
		thickness) with temperature)) and plasma) and ((measur\$4 or compar\$3 or determin\$3) with (depth or thickness))) and ((depth		
		or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or		
		temperature.clm.)	USPAT	2002/09/11
_	454	thickness) with temperature)) and plasma) and ((measur\$4 or compar\$3 or determin\$3)	051111	16:04
	•	with (depth or thickness))) and ((depth or thickness).ab. (depth or		1
		thickness).ab. (depth of thickness).clm.)) and (temperature.ab. or temperature.clm.)) and (etch or etching)		
_	214		USPAT	2002/09/11
		and ((measur\$4 or compar\$3 or determin\$3)		
		with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or		
		thickness).cim.)) and (temperature.ab. of temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)		
_	214		USPAT	2002/09/12 08:45
		and ((measur\$4 or compar\$3 or determin\$3) with (depth or thickness))) and ((depth		
		or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or		
		thickness).clm.)) and (temperature.ds. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.))		
	214	and @ay<=2001	USPAT	2004/01/23
_	213	thickness) with temperature)) and plasma) and ((measur\$4 or compar\$3 or determin\$3)		13:57
		with (depth or thickness))) and ((depth or thickness).ab. (depth or		
	ļ	thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or		
		etching).ab. or (etch or etching).clm.)) and @ay<=2001		
	_ 1	lama cal.		

			USPAT	2002/09/12
-	183	<pre>(((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur\$4 or compar\$3 or determin\$3) with (depth or thickness))) and ((depth</pre>	USPAT	11:40
		or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or		
		etching).ab. or (etch or etching).clm.))		
_	751	and @ay<=2001) and @py<=2001 fulford	USPAT	2002/09/12
_	315	fulford.in.	USPAT	2002/09/12
_	0	fulford-Jim.in.	USPAT	2002/09/12
-	2	fulford-Jim-H.in.	USPAT	2002/09/12
-	2	("5733812" "5789780").PN.	USPAT	2002/09/12
-	9	5863824.URPN.	USPAT	2002/09/12
_	504	fulford and semiconductor	USPAT	2002/09/12
_	266	fulford.in. and semiconductor	USPAT	2002/09/12
_	254	(fulford.in. and semiconductor) and	USPAT	2002/09/12
_	192	(depth or thickness) ((fulford.in. and semiconductor) and (depth or thickness)) and @py<=2000	USPAT	2002/09/12
_	142	(depth and thickness) with temperature with (change or changing or adjust\$3 or	USPAT	2002/09/12 13:59
_	40	vary or varied or varing) ((depth and thickness) with temperature with (change or changing or adjust\$3 or vary or varied or varing)) and	USPAT	2002/09/12 13:40
-	8085	semiconductor (depth or thickness) with temperature with (change or changing or adjust\$3 or vary or varied or varing)	ÚSPÁT	2002/09/12 14:02
_	1783	((depth or thickness) with temperature with (change or changing or adjust\$3 or vary or varied or varing)) and	USPAT	2002/09/12 14:00
-	551	semiconductor (((depth or thickness) with temperature with (change or changing or adjust\$3 or vary or varied or varing)) and	USPAT	2002/09/12 14:01
-	527	semiconductor) and plasma ((((depth or thickness) with temperature with (change or changing or adjust\$3 or	USPAT	2002/09/12 14:01
		<pre>vary or varied or varing)) and semiconductor) and plasma) not ((((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur\$4 or compar\$3 or determin\$3) with (depth or thickness))) and ((depth</pre>		
		or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.))		
		and @ay<=2001) and @py<=2001)		

-	514	(((((depth or thickness) with temperature with (change or changing or adjust\$3 or vary or varied or varing)) and	USPAT	2002/09/12 14:01
		semiconductor) and plasma) not		
		(((((((semiconductor and ((depth or		
		thickness) with temperature)) and plasma)		
		<pre>and ((measur\$4 or compar\$3 or determin\$3) with (depth or thickness))) and ((depth</pre>		
		or thickness).ab. (depth or		
		thickness).clm.)) and (temperature.ab. or		
		temperature.clm.)) and ((etch or		
		etching).ab. or (etch or etching).clm.)) and @ay<=2001) and @py<=2001)) not		
		(((depth and thickness) with temperature		
		with (change or changing or adjust\$3 or		
]		vary or varied or varing)) and		
		semiconductor)	USPAT	2002/09/12
-	372	<pre>(((((depth or thickness) with temperature with (change or changing or</pre>	OSFAI	14:03
		adjust\$3 or vary or varied or varing))		
		and semiconductor) and plasma) not		
		(((((((semiconductor and ((depth or		
]		thickness) with temperature)) and plasma) and ((measur\$4 or compar\$3 or determin\$3)		
		with (depth or thickness))) and ((depth		
		or thickness).ab. (depth or		
		thickness).clm.)) and (temperature.ab. or		
		temperature.clm.)) and ((etch or		
		etching).ab. or (etch or etching).clm.)) and @ay<=2001) and @py<=2001)) not		
		(((depth and thickness) with temperature		
		with (change or changing or adjust\$3 or		
		vary or varied or varing)) and		
	271	<pre>semiconductor)) and (etch or etching) (((((((depth or thickness) with</pre>	USPAT	2002/09/12
_	372	temperature with (change or changing or		14:04
		adjust\$3 or vary or varied or varing))	Ì	
		and semiconductor) and plasma) not		
		<pre>((((((((semiconductor and ((depth or thickness) with temperature)) and plasma)</pre>		
		and ((measur\$4 or compar\$3 or determin\$3)		
		with (depth or thickness))) and ((depth		
		or thickness).ab. (depth or		
		thickness).clm.)) and (temperature.ab. or		
		<pre>temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.))</pre>		
		and @ay<=2001) and @py<=2001)) not		
		(((depth and thickness) with temperature		
		with (change or changing or adjust\$3 or		
		<pre>vary or varied or varing)) and semiconductor)) and (etch or etching))</pre>		
	ļ	and @ay<=2001		
-	370	(((((((depth or thickness) with	USPAT	2002/09/12
	1	temperature with (change or changing or		14:04
	1	adjust\$3 or vary or varied or varing)) and semiconductor) and plasma) not		
		(((((((semiconductor and ((depth or		
		thickness) with temperature)) and plasma)		
		and ((measur\$4 or compar\$3 or determin\$3)		
		with (depth or thickness))) and ((depth		
		or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or		
		temperature.clm.)) and ((etch or		
		etching).ab. or (etch or etching).clm.))		
		and @ay<=2001) and @py<=2001)) not (((depth and thickness) with temperature		
		with (change or changing or adjust\$3 or		
		vary or varied or varing)) and		
		semiconductor)) and (etch or etching))		
		and @ay<=2001) not fulford.in.	L	

S68 (((((((((depth or thickness) with temperature with (change or changing or adjust\$3 or vary or varied or varing)) and semiconductor) and plasma) not ((((((((semiconductor and ((depth or thickness))) and ((depth or thickness)), ab. (depth or thickness), ab. or (etch or etching).alm.)) and @ay<=2001) and @py<=2001)) not (((depth and thickness)) and ((etch or etching)) and @ay<=2001) and @py<=2001)) not (((((((semiconductor and ((depth or thickness)))) and (etch or etching)) and @ay<=2001 not fullord.in.) not ((((((((semiconductor and ((depth or thickness)))) and ((etch or etching)) and ((etch or etching)) and ((etch or etching)) and ((etch or etching)) and ((etch or etching).alm.)) and (etch or etching).alm.) and (etch or etching).al	- 368	(((((((depth or thickness) with	USPAT 1	2002/09/12
and @ay<=2001)) and (opening or trench	- 232	temperature with (change or changing or adjust\$3 or vary or varied or varing)) and semiconductor) and plasma) not ((((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur\$4 or compar\$3 or determin\$3) with (depth or thickness).ab. (depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @gy<=2001) not (((depth and thickness) with temperature with (change or changing or adjust\$3 or vary or varied or varing)) and semiconductor) and (etch or etching) and @gy<=2001) not fulford.in.) not (((((((semiconductor and ((depth or thickness) with temperature)) and plasma) and ((measur\$4 or compar\$3 or determin\$3) with (depth or thickness).ab. (depth or thickness).clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @gy<=2001) ((((((((((depth or thickness) with temperature.ab. or temperature with (change or changing or adjust\$3 or vary or varied or varing)) and semiconductor) and plasma) not (((((((((semiconductor and ((depth or thickness) with temperature with (change or changing or adjust\$3 or vary or varied or varing)) and semiconductor) and plasma) not ((((((((semiconductor and ((depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and (fetch or etching).ab. or (etch or etching).clm.)) and @gy<=2001) not fulford.in.) not (((depth and thickness) with temperature with (change or changing or adjust\$3 or vary or varied or varing)) and semiconductor) and (etch or etching) and @ay<=2001) not fulford.in.) not ((((((semiconductor and ((depth or thickness) with temperature with (change or changing or adjust\$3 or vary or varied or varing)) and semiconductor) and (etch or etching) and (measur\$4 or compar\$3 or determin\$3) with (depth or thickness) with temperature.ab. or temperature.clm.)) and (temperature.ab. or temperature.clm.)) and (temperature.ab. or temperature.clm.)) and (temperature.ab. or temperature.clm.)) and (fetch or etching).ab. or (etch or etching).clm.))	USPAT	2002/09/12

	203	<pre>((((((((((((((((((((((((((((((((((((</pre>	USPAT	2002/09/12 14:14
		and @ay<=2001) and @py<=2001)) not (((depth and thickness) with temperature with (change or changing or adjust\$3 or vary or varied or varing)) and semiconductor)) and (etch or etching)) and @ay<=2001) not fulford.in.) not ((((((semiconductor and ((depth or thickness) with temperature)) and plasma)		
		and ((measur\$4 or compar\$3 or determin\$3) with (depth or thickness))) and ((depth or thickness).ab. (depth or thickness).clm.)) and (temperature.ab. or temperature.clm.)) and ((etch or etching).ab. or (etch or etching).clm.)) and @ay<=2001)) and (opening or trench or hole)) and (measur\$4 or compar\$3 or		
_	141	<pre>determin\$3) ((depth or thickness).ab. with temperature) and semiconductor and plasma</pre>	USPAT	2004/02/02 17:33
_	1	5375064.pn.	USPAT	2002/09/16 14:29
_	4	5375064.URPN.	USPAT	2002/09/16 13:06
_	5	("5082517" "5375064" "5376224" "5680014" "5688415").PN.	USPAT	2002/09/16
	14462	(temperature with control or controller) same (depth or thickness)	USPAT	2002/09/16
-	840	((temperature with control or controller) same (depth or thickness)) and semiconductor and plasma and ((contact adj hole) or opening or via or trench)	USPAT	2002/09/16
<u>-</u>	247	(((temperature with control or controller) same (depth or thickness)) and semiconductor and plasma and ((contact adj hole) or opening or via or trench)) and photo\$1resist	USPAT	2002/09/16 13:19
-	244	<pre>((((temperature with control or controller) same (depth or thickness)) and semiconductor and plasma and ((contact adj hole) or opening or via or trench)) and photo\$lresist) not (((depth or thickness).ab. with temperature) and semiconductor and plasma)</pre>	USPAT	2002/09/16 13:22
-	233	((((temperature with control or controller) same (depth or thickness)) and semiconductor and plasma and ((contact adj hole) or opening or via or trench)) and photo\$1resist) not (((depth or thickness).ab. with temperature) and semiconductor and plasma)) and (etch or etching)	USPAT	2002/09/16 13:22

		·		
	98	<pre>((((((temperature with control or controller) same (depth or thickness))</pre>	USPAT	2002/09/16 14:29
		<pre>and semiconductor and plasma and ((contact adj hole) or opening or via or trench)) and photo\$1resist) not (((depth</pre>		
		or thickness).ab. with temperature) and semiconductor and plasma)) and (etch or etching)) and (temperature with (zone or		
_	0	area or region)) 364/474.3.ccls.	USPAT	2002/09/16
_	0	364/474.ccls.	USPAT	2002/09/16 14:31
_	0	700/188.pn.	USPAT	2002/09/16 14:32
_	176	700/188.ccls.	USPAT	2002/09/16 14:32
_	7	700/188.ccls. and semiconductor	USPAT	2002/09/16 14:34
_	189	216/59.ccls.	USPAT	2002/09/16 14:35
-	117	216/59.ccls. and temperature	USPAT	2002/09/16 14:35
_	117	(216/59.ccls. and temperature) not ((((((temperature with control or controller) same (depth or thickness)) and semiconductor and plasma and	USPAT	2002/09/16 14:35
		<pre>((contact adj hole) or opening or via or trench)) and photo\$1resist) not (((depth or thickness).ab. with temperature) and semiconductor and plasma)) and (etch or etching)) and (temperature with (zone or</pre>		
-	116	area or region))) (216/59.ccls. and temperature) not (((depth or thickness).ab. with temperature) and semiconductor and	USPAT	2002/09/16 14:35
-	87	plasma) ((216/59.ccls. and temperature) not (((depth or thickness).ab. with temperature) and semiconductor and	USPAT	2002/09/16 14:36
-	2	plasma)) and (depth or thickness) 5795493.pn. 5375064.pn.	USPAT	2003/10/03
_	3	Fulford-Jim-H.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/23 13:52
_	13	Lansford-Jeremy.in.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/23 13:54
_	64617	semiconductor and ((depth or thickness) same temperature)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/23 14:06
_	20409	(semiconductor and ((depth or thickness) same temperature)) and @ay<=2001 and plasma	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/23 14:07
_	25790	semiconductor and ((depth or thickness) with temperature)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/23 14:07
1	1	I .	IBM TDB	

	7495	(semiconductor and ((depth or thickness)	USPAT;	2004/01/23
		with temperature)) and @ay<=2001 and	US-PGPUB;	14:11
		plasma	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/01/22
-	2890	((semiconductor and ((depth or thickness)	USPAT;	2004/01/23
		with temperature)) and @ay<=2001 and	US-PGPUB;	14:25
		plasma) and ((measur\$4 or compar\$3 or	EPO; JPO;	
		determin\$3 or calulat\$3) with (depth or	DERWENT;	
		thickness))	IBM_TDB	0004/01/02
-	668	((semiconductor and ((depth or thickness)	USPAT;	2004/01/23
		with temperature)) and @ay<=2001 and	US-PGPUB;	14:26
		plasma) and ((measur\$4 or compar\$3 or	EPO; JPO;	
		determin\$3 or calulat\$3) with (depth or	DERWENT;	
		thickness) with temperature)	IBM_TDB	
_	474	(((semiconductor and ((depth or	USPAT;	2004/01/23
		thickness) with temperature)) and	US-PGPUB;	14:34
		@av<=2001 and plasma) and ((measur\$4 or	EPO; JPO;	
		compar\$3 or determin\$3 or calulat\$3) with	DERWENT;	
		(depth or thickness) with temperature))	IBM_TDB	
		and (etch or etching)	_	
_	392	((((semiconductor and ((depth or	USPAT;	2004/02/02
	""	thickness) with temperature)) and	US-PGPUB;	16:32
		@ay<=2001 and plasma) and ((measur\$4 or	EPO; JPO;	
		compar\$3 or determin\$3 or calulat\$3) with	DERWENT;	
		(depth or thickness) with temperature))	IBM TDB	
		and (etch or etching)) and @ad<=20010327		
	474	((((semiconductor and ((depth or	USPAT;	2004/02/02
_	4/4	thickness) with temperature)) and	US-PGPUB;	16:33
		@ay<=2001 and plasma) and ((measur\$4 or	EPO; JPO;	
		compar\$3 or determin\$3 or calulat\$3) with	DERWENT;	1
		(depth or thickness) with temperature))	IBM TDB	
		and (etch or etching))	1511_155	
	1006		USPAT;	2004/02/02
_	1806	(depth or thickness) with temperature	US-PGPUB;	16:33
		with (etch or etching)	EPO; JPO;	10.33
			DERWENT;	
			IBM TDB	
ļ	670	//double on thiskness with tamparature	USPAT;	2004/02/02
-	678	((depth or thickness) with temperature	USPAI; US-PGPUB;	16:33
		with (etch or etching)) and plasma		10.33
			EPO; JPO; DERWENT;	
	1		IBM_TDB USPAT;	2004/02/02
-	594	(((depth or thickness) with temperature		
		with (etch or etching)) and plasma) and	US-PGPUB;	16:34
		@ay<=2001	EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	0004/00/00
-	396	((depth or thickness).ab. with	USPAT;	2004/02/02
		temperature) and semiconductor and plasma	US-PGPUB;	17:33
			EPO; JPO;	
			DERWENT;	!
			IBM_TDB	
	371	(((depth or thickness).ab. with	USPAT;	2004/02/02
	1	temperature) and semiconductor and plasma	US-PGPUB;	17:34
1) and @ay<=2001	EPO; JPO;	1
		, , , , , , , , , , , , , , , , , , , ,	DERWENT;	
			IBM TDB	